MBR3045ST, MBRB3045CT-1

Switch-mode Power Rectifier

Features and Benefits

- Dual Diode Construction Terminals 1 and 3 May Be Connected for Parallel Operation at Full Rating
- 45 V Blocking Voltage
- Low Forward Voltage Drop
- 175°C Operating Junction Temperature
- These are Pb-Free Devices

Applications

- Power Supply Output Rectification
- Power Management
- Instrumentation

Mechanical Characteristics

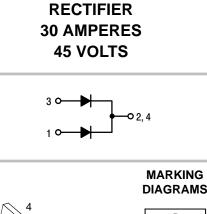
- Case: Epoxy, Molded
- Weight (Approximately): 1.9 Grams (TO-220)

1.5 Grams (TO-262)

- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- Epoxy Meets UL 94 V-0 @ 0.125 in

MAXIMUM RATINGS

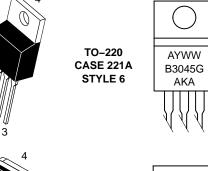
Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	45	V
Average Rectified CurrentPer Device $(T_C = 130^{\circ}C)$ Per Diode	I _{F(AV)}	30 15	A
Peak Repetitive Forward Current, per Diode (Square Wave, $V_R = 45 V$, 20 kHz)	I _{FRM}	30	A
Non-Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions, Halfwave, Single Phase, 60 Hz)	I _{FSM}	150	A
Peak Repetitive Reverse Current, per Diode (2.0 μ s, 1.0 kHz)	I _{RRM}	2.0	A
Storage Temperature Range	T _{stg}	–65 to +175	°C
Operating Junction Temperature (Note 1)	TJ	–65 to +175	°C
Peak Surge Junction Temperature (Forward Current Applied)	T _{J(pk)}	175	°C
Voltage Rate of Change (Rated V _R)	dv/dt	10,000	V/µs



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ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The heat generated must be less than the thermal conductivity from Junction-to-Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.

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THERMAL CHARACTERISTICS (Per Diode)

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction to Case	$R_{ extsf{ heta}JC}$	1.5	°C/W

ELECTRICAL CHARACTERISTICS (Per Diode)

Characteristic	Symbol	Value	Unit
Instantaneous Forward Voltage (Note 2) ($i_F = 15 \text{ Amp}, T_C = 25^{\circ}C$) ($i_F = 15 \text{ Amp}, T_C = 125^{\circ}C$) ($i_F = 30 \text{ Amp}, T_C = 25^{\circ}C$) ($i_F = 30 \text{ Amp}, T_C = 125^{\circ}C$)	VF	0.62 0.57 0.76 0.72	V
Instantaneous Reverse Current (Note 2) $(V_R = 45 \text{ Volts}, T_C = 25^{\circ}\text{C})$ $(V_R = 45 \text{ Volts}, T_C = 125^{\circ}\text{C})$	IR	0.2 40	mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2 Pulse Test: Pulse Width = $300 \,\mu$ s, Duty Cycle $\leq 2.0\%$

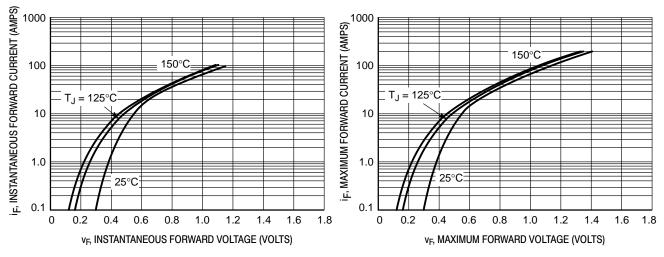


Figure 1. Typical Forward Voltage

Figure 2. Maximum Reverse Current

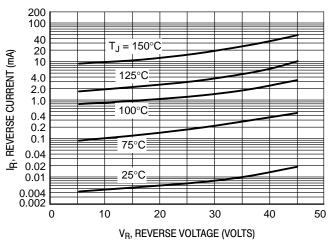


Figure 3. Typical Reverse Current

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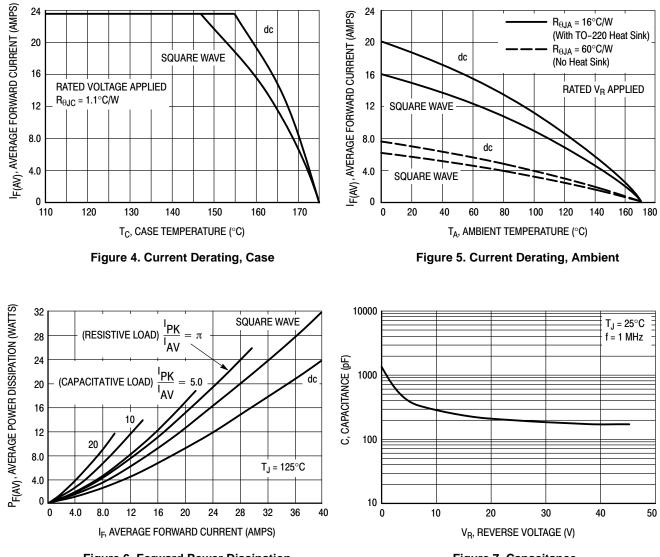


Figure 6. Forward Power Dissipation

Figure 7. Capacitance

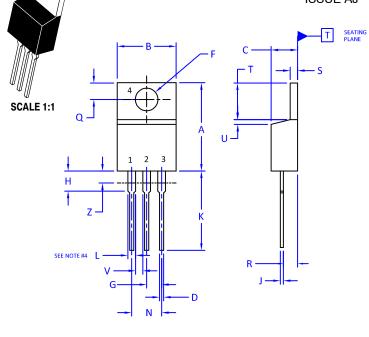
ORDERING INFORMATION

Device	Package	Shipping
MBR3045STG	TO–220 (Pb–Free)	50 Units/Rail
MBRB3045CT-1G	TO-262 (Pb-Free)	50 Units/Rail

DATE 05 NOV 2019



TO-220 CASE 221A-09 ISSUE AJ



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 2009.

2. CONTROLLING DIMENSION: INCHES

3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

4. MAX WIDTH FOR F102 DEVICE = 1.35MM

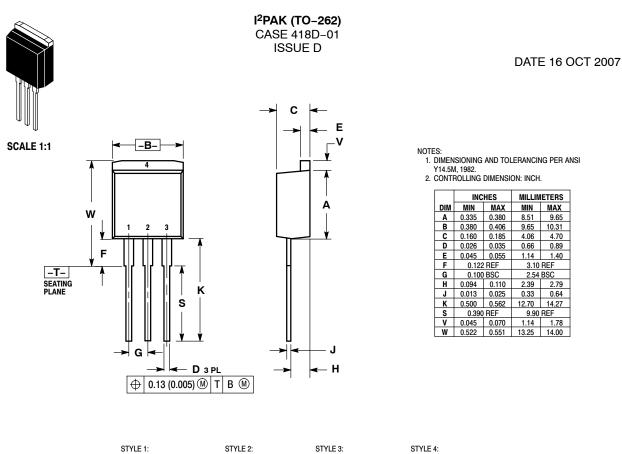
	INCHES		MILLIME	ETERS
DIM	MIN.	MAX.	MIN.	MAX.
А	0.570	0.620	14.48	15.75
В	0.380	0.415	9.66	10.53
С	0.160	0.190	4.07	4.83
D	0.025	0.038	0.64	0.96
F	0.142	0.161	3.60	4.09
G	0.095	0.105	2.42	2.66
Н	0.110	0.161	2.80	4.10
J	0.014	0.024	0.36	0.61
К	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
Ν	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.41
Т	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045		1.15	
Z		0.080		2.04

STYLE 1: PIN 1. 2. 3. 4.	COLLECTOR EMITTER	STYLE 2: PIN 1. 2. 3. 4.	EMITTER	3.	CATHODE ANODE GATE ANODE	STYLE 4: PIN 1. 2. 3. 4.	MAIN TERMINAL 1 MAIN TERMINAL 2 GATE MAIN TERMINAL 2
STYLE 5: PIN 1. 2. 3. 4.	DRAIN SOURCE	2. 3.	ANODE CATHODE ANODE CATHODE	2. 3.	CATHODE ANODE CATHODE ANODE	STYLE 8: PIN 1. 2. 3. 4.	••••••
STYLE 9: PIN 1. 2. 3. 4.	COLLECTOR EMITTER	STYLE 10: PIN 1. 2. 3. 4.	GATE SOURCE DRAIN	STYLE 11: PIN 1. 2. 3. 4.	DRAIN SOURCE GATE	STYLE 12 PIN 1. 2. 3. 4.	MAIN TERMINAL 1 MAIN TERMINAL 2 GATE NOT CONNECTED

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STYLE 1:		STYLE 2:		STYLE 3:		STYLE 4:	
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2.	COLLECTOR	2.	DRAIN	2.	CATHODE	2.	COLLECTOR
3.	EMITTER	3.	SOURCE	3.	ANODE	3.	EMITTER
4.	COLLECTOR	4.	DRAIN	4.	CATHODE	4.	COLLECTOR

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